

Agilent MGA-565P8 20 dBm P_{sat} High Isolation Buffer Amplifier

Data Sheet

Description

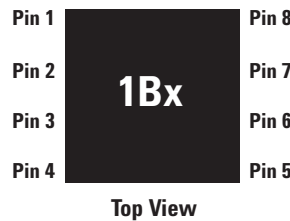
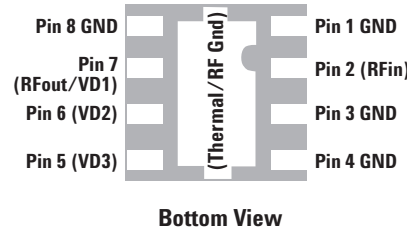
The MGA-565P8 is designed for use in LO chains to drive high dynamic range passive mixers. It provides high isolation, high gain, and consistent output power. It is a GaAs MMIC, fabricated using Agilent Technologies' cost effective, reliable enhancement mode PHEMT (Pseudomorphic High Electron Mobility Transistor)^[1] process. This device is housed in the LPCC 2x2 mm package. This package offers good thermal dissipation and RF characteristics.

MGA-565P8 features a saturated power of 20 dBm (with 0 dBm input power) and reverse isolation in excess of 40 dB at 2 GHz. The saturated output power can be set between 9 dBm and 20 dBm using an external resistor, with a corresponding adjustment in current consumption.

Notes:

1. Enhancement mode technology employs a single positive V_{gs} , eliminating the need of negative gate voltage associated with conventional depletion mode devices.
2. Conform to JEDEC reference outline MO229 for DRP-N

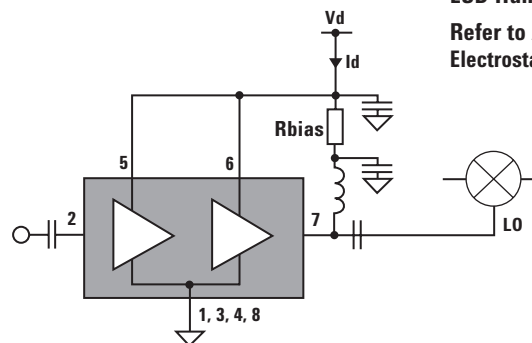
Pin Connections and Package Marking



Note:
Package marking provides orientation and identification

"1B" = Device Code
"x" = Data code indicates the month of manufacture.

Simplified Schematic



Features

- Up to 3.5 GHz operating frequency
- 2:1 VSWR input and output at 2GHz
- Small package size: 2.0 x 2.0 x 0.75 mm LPCC^[3]
- MSL-1 and lead-free
- Tape-and-reel packaging option available

Specifications

@ 2 GHz, $V_d = 5V$, $P_{in} = 0$ dBm

- $P_{sat} = 20$ dBm
- $I_{dsat} = 67$ mA
- Isolation = 42 dB
- Small Signal Gain = 22 dB

Applications

- VCO buffer amplifier for Cellular/PCS or other wireless infrastructures



Attention:
Observe precautions for handling electrostatic sensitive devices.

ESD Machine Model (Class A)

ESD Human Body Model (Class 0)

Refer to Agilent Application Note A004R: Electrostatic Discharge Damage and Control.



Agilent Technologies

MGA-565P8 Absolute Maximum Ratings^[1]

Symbol	Parameter	Units	Absolute Maximum
V_d	DC Supply Voltage	V	8
P_{diss}	Total Power Dissipation ^[2]	mW	448
$P_{in\ max.}$	RF Input Power ($V_d=5V$)	dBm	15
T_{CH}	Channel Temperature	°C	150
T_{STG}	Storage Temperature	°C	-65 to 150
θ_{ch_b}	Thermal Resistance ^[3]	°C/W	91
	ESD (Human Body Model)	V	100
	ESD (Machine Model)	V	30

Notes:

1. Operation of this device in excess of any one of these parameters may cause permanent damage.
2. Board (package belly) temperature T_B is 25°C. Derate 11 mW/°C for $T_B > 109^\circ\text{C}$.
3. Channel-to-board thermal resistance measured using 150°C Liquid Crystal Measurement method.

Electrical Specifications

$T_A = 25^\circ\text{C}$, Frequency = 2 GHz, $R_{bias} = 0\Omega$ (unless specified otherwise)

Symbol	Parameter and Test Condition	Units	Min.	Typ.	Max.	
P_{sat}	Saturated Power at 0 dBm input	$V_d = 5V^{[1]}$	dBm	18.5	20	20.6
		$V_d = 3V$	dBm		17	
I_{dsat}	Saturation Current	$V_d = 5V^{[1]}$	mA	58	67	78
		$V_d = 3V$	mA		45	
ISL ^[1]	Reverse Isolation	dB	42	50		
Gain	Small Signal Gain	$V_d = 5V^{[1]}$	dB	20	21.8	23.5
		$V_d = 3V$			20	
I_{ds}	Small Signal Current ($P_{in} = -10\ \text{dBm}$)	$V_d = 5V^{[1]}$	mA	33	37	43
		$V_d = 3V$	dB		27	
RL ^[1]	Return Loss	Input			-8	
		Output			-10	

Notes:

1. Typical value determined from a sample size of 500 parts from 3 wafers.
2. Measurement obtained using production test board described in the block diagram below. Circuit losses have been de-embedded from actual measurements.

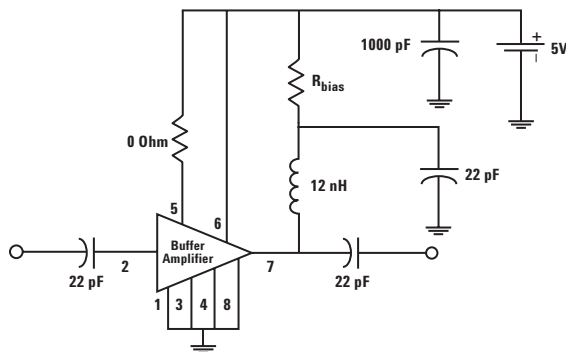


Figure 1. Production Test Circuit Schematic at 2 GHz..

Product Consistency Distribution Charts at 2 GHz^[1, 2]

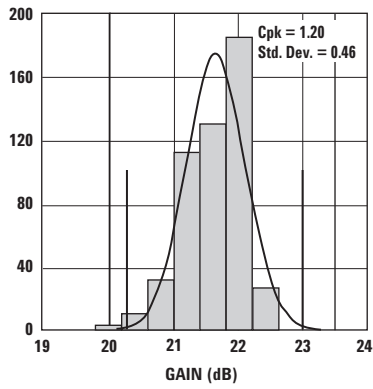


Figure 2. Gain Distribution.
LSL = 20.0 dB, USL = 23.5 dB.

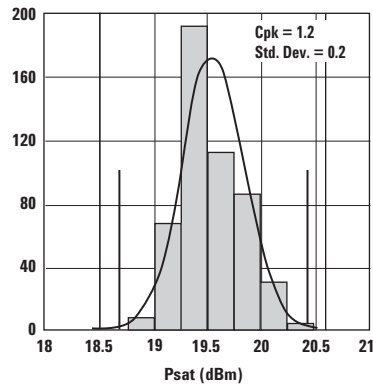


Figure 3. Psat Distribution.
LSL = 18.5 dBm, USL = 20.6

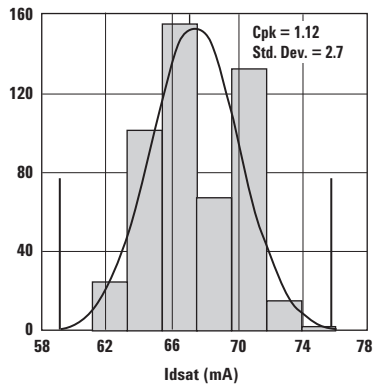


Figure 4. Idsat Distribution.
LSL = 58.0 dBm, USL = 78.0 dBm.

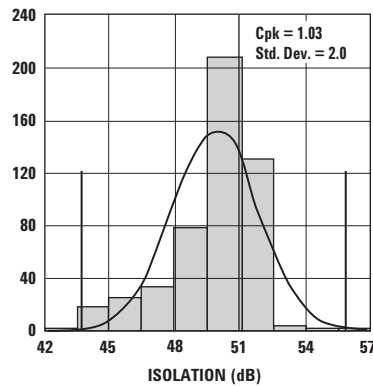


Figure 5. Isolation Distribution.
LSL = 42.0 dB, USL = 56.0 dB.

Notes:

1. Statistical distribution determined from a sample size of 500 parts from 3 wafers.
2. Future wafers allocated to this product may have typical values anywhere between the minimum and maximum specification limits.

MGA-565P8 Typical Performance Curves (at 25°C, 2 GHz, $R_{bias} = 0\Omega$, unless specified otherwise)

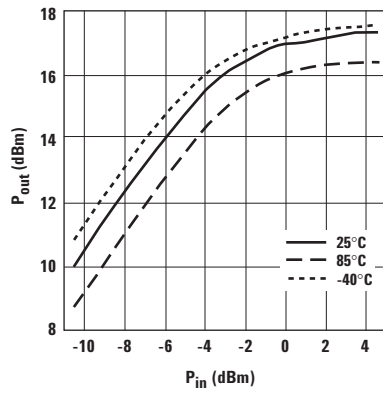


Figure 6. P_{out} vs. P_{in} , $V_d = 3V$.

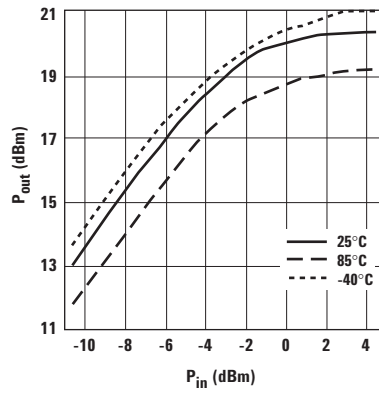


Figure 7. P_{out} vs. P_{in} , $V_d = 5V$.

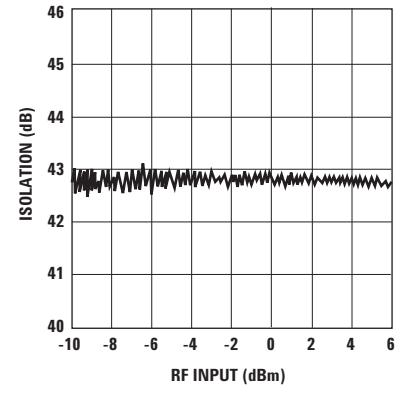


Figure 8. Isolation vs P_{in} , $V_d = 3V$.

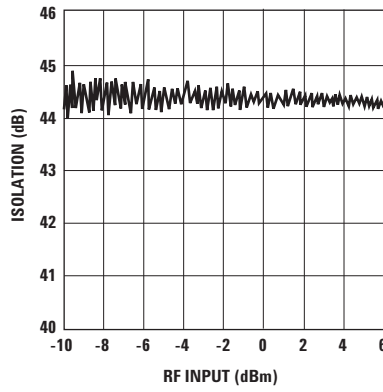


Figure 9. Isolation vs. P_{in} , $V_d = 5V$.

MGA-565P8 Typical Performance Curves ($R_{bias} = 0\Omega$, temperature variation)

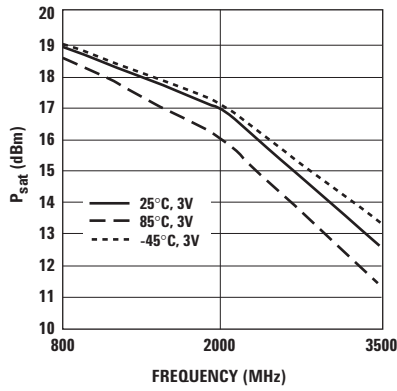


Figure 10. P_{sat} vs. Frequency.
($P_{in} = 0$ dBm, $V_d = 3$ V)

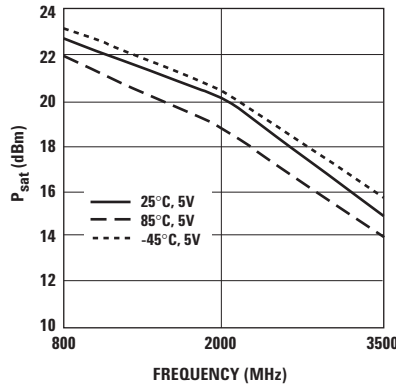


Figure 11. P_{sat} vs. Frequency.
($P_{in} = 0$ dBm, $V_d = 5$ V)

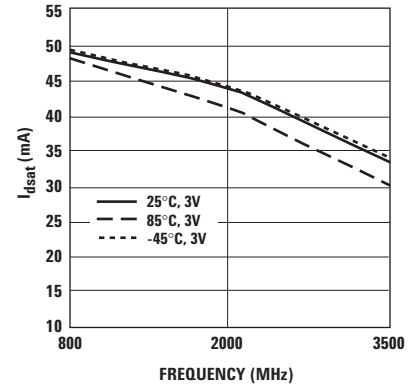


Figure 12. I_{dsat} vs. Frequency.
($P_{in} = 0$ dBm, $V_d = 3$ V)

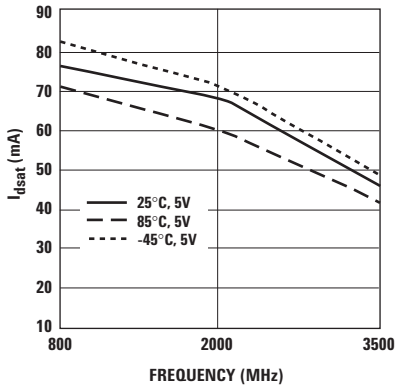


Figure 13. I_{dsat} vs. Frequency.
($P_{in} = 0$ dBm, $V_d = 5$ V)

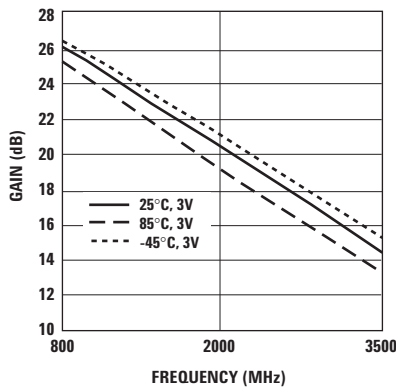


Figure 14. Gain vs. Frequency.
($P_{in} = -10$ dBm, $V_d = 3$ V)

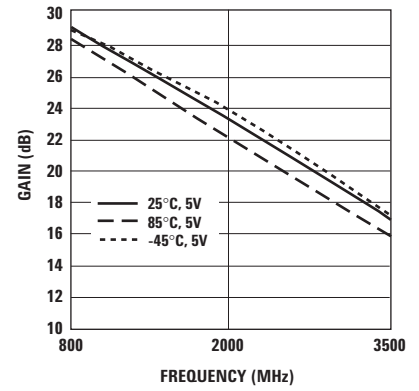


Figure 15. Gain vs. Frequency.
($P_{in} = -10$ dBm, $V_d = 5$ V)

MGA-565P8 Typical Performance Curves ($R_{bias} = 0\Omega$, temperature variation), continued

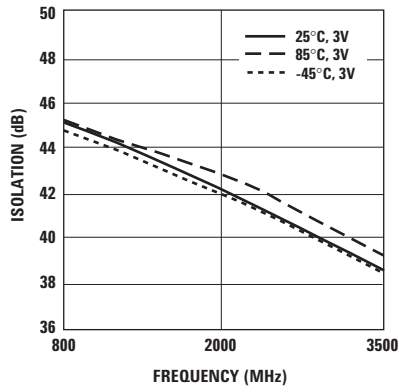


Figure 16. Isolation vs. Frequency.
($P_{in} = -10$ dBm, $V_d = 3$ V)

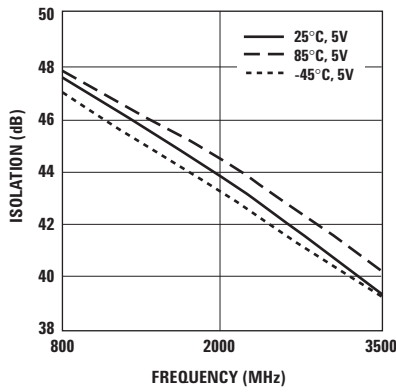


Figure 17. Isolation vs. Frequency.
($P_{in} = -10$ dBm, $V_d = 5$ V)

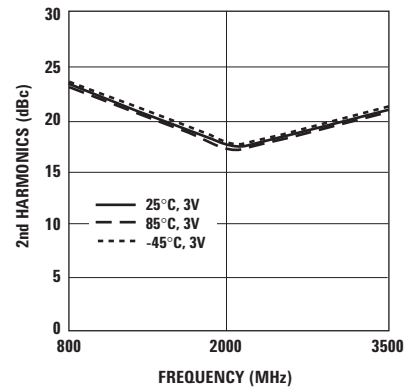


Figure 18. Second Harmonics vs. Frequency.
($P_{in} = 0$ dBm, $V_d = 3$ V)

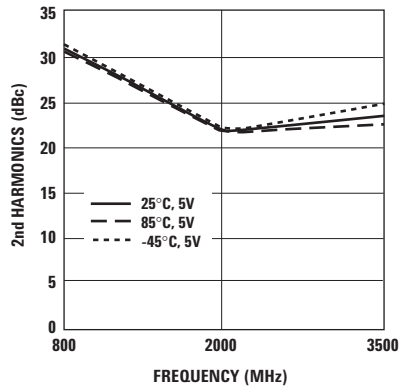


Figure 19. Second Harmonics vs. Frequency.
($P_{in} = 0$ dBm, $V_d = 5$ V)

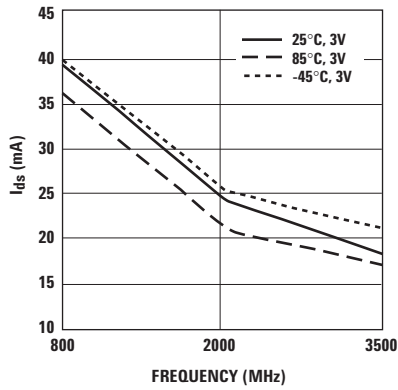


Figure 20. I_{ds} vs. Frequency.
($P_{in} = -10$ dBm, $V_d = 3$ V)

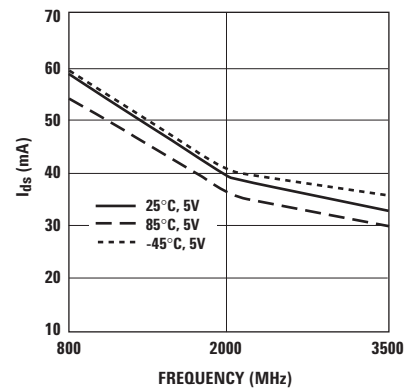


Figure 21. I_{ds} vs. Frequency.
($P_{in} = -10$ dBm, $V_d = 5$ V)

MGA-565P8 Typical Performance Curves (at 25°C, 2 GHz, unless specified otherwise)

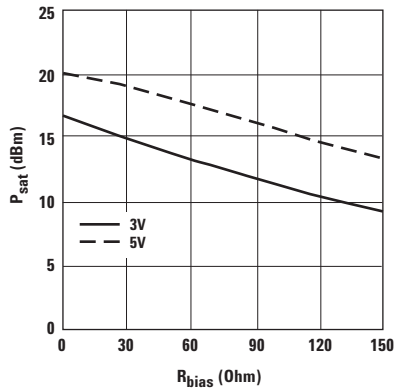


Figure 22. P_{sat} vs. R_{bias},
P_{in} = 0 dBm for V_d = 3V and 5V.

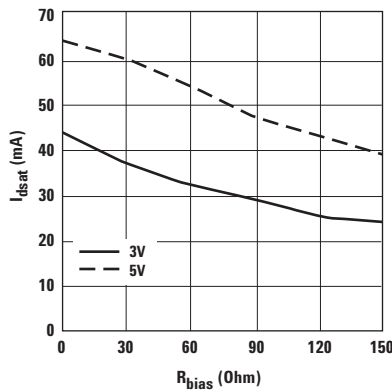


Figure 23. I_{dsat} vs. R_{bias},
P_{in} = 0 dBm for V_d = 3V and 5V.

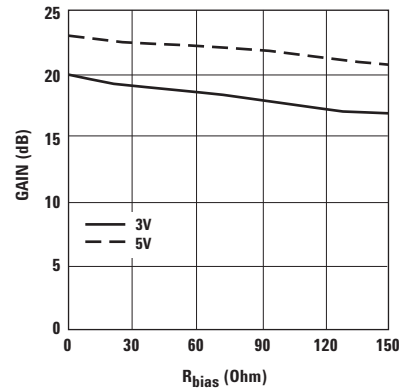


Figure 24. Gain vs. R_{bias},
P_{in} = -10 dBm for V_d = 3V and 5V.

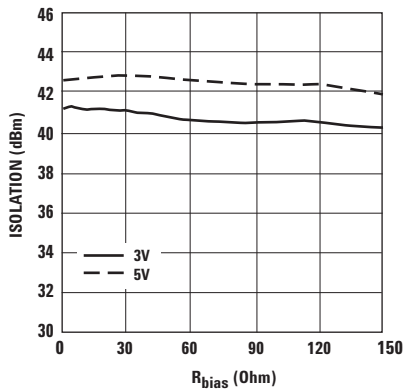


Figure 25. Isolation vs. R_{bias},
P_{in} = -10 dBm for V_d = 3V and 5V.

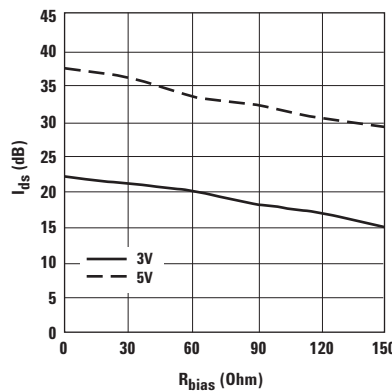


Figure 26. I_{ds} vs. R_{bias},
P_{in} = -10 dBm for V_d = 3V and 5V.

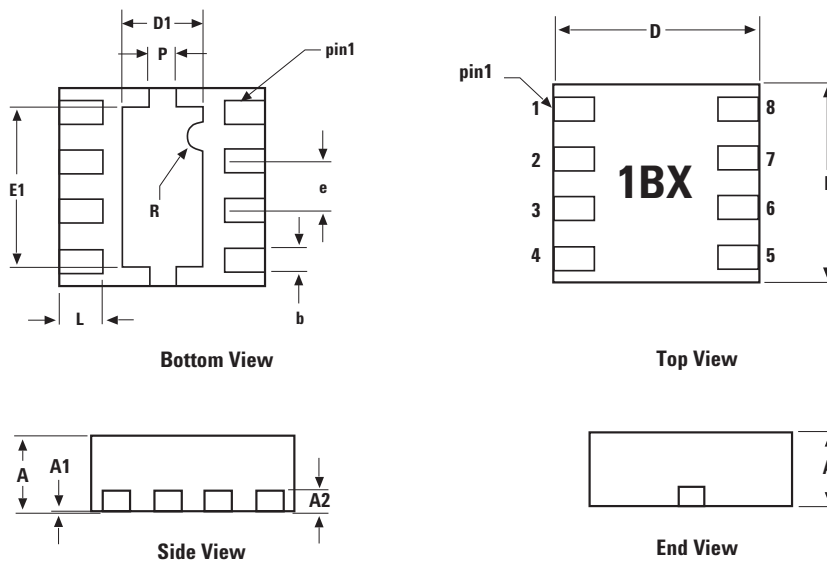
Device Models

Refer to Agilent's Web Site
www.agilent.com/view/rf

Ordering Information

Part Number	No. of Devices	Container
MGA-565P8-TR1	3000	7" Reel
MGA-565P8-TR2	10000	13" Reel
MGA-565P8-BLK	100	antistatic bag

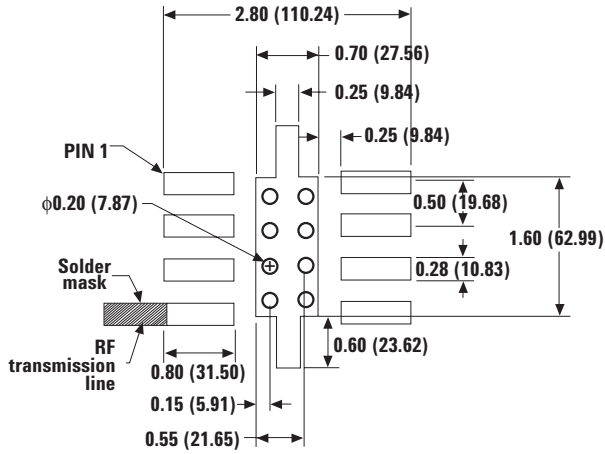
2x2 LPCC (JEDEC DFP-N) Package Dimensions



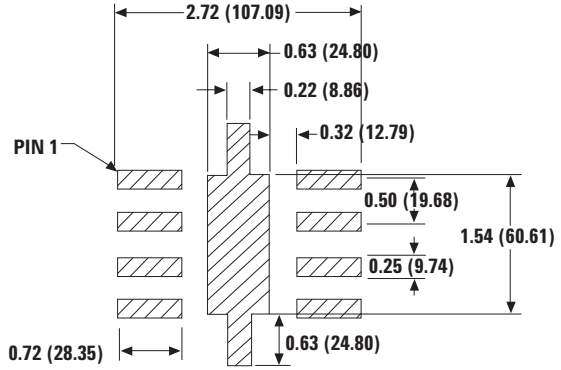
SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0	0.02	0.05
A2		0.203 REF	
b	0.225	0.25	0.275
D	1.9	2.0	2.1
D1	0.65	0.80	0.95
E	1.9	2.0	2.1
E1	1.45	1.6	1.75
e		0.50 BSC	

DIMENSIONS ARE IN MILLIMETERS

PCB Land Pattern and Stencil Design



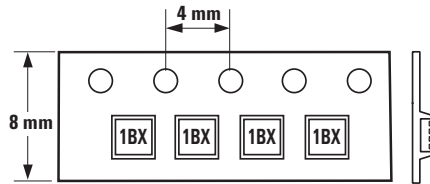
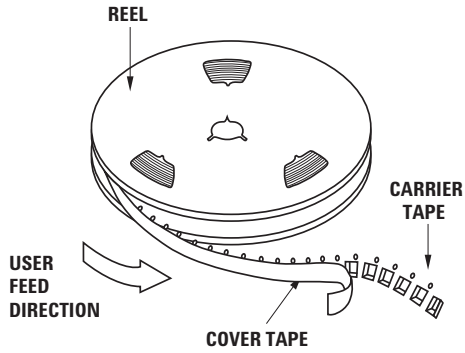
PCB Land Pattern (top view)



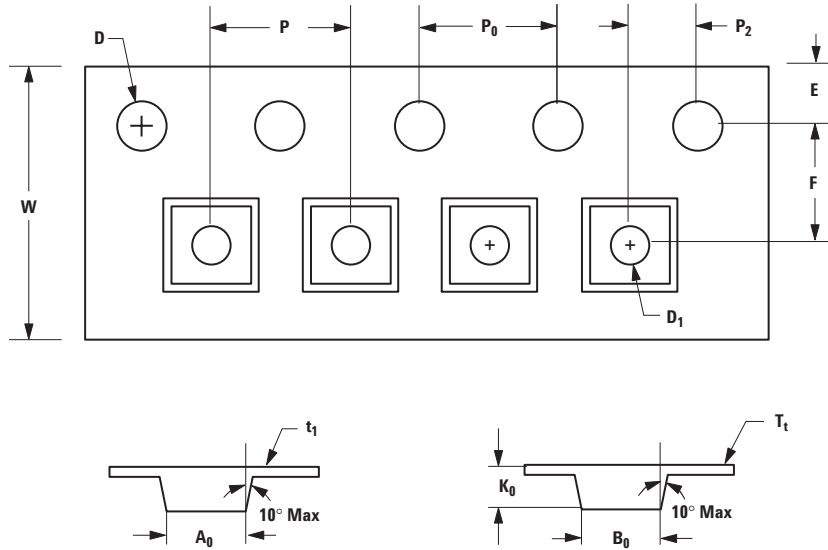
Stencil Layout (top view)

Notes: Typical stencil thickness is 5 mils.
Measurements are in millimeters (mils).

Device Orientation



Tape Dimensions



DESCRIPTION		SYMBOL	SIZE (mm)	SIZE (inches)
CARRIER TAPE	LENGTH	A ₀	2.30 ± 0.05	0.091 ± 0.004
	WIDTH	B ₀	2.30 ± 0.05	0.091 ± 0.004
	DEPTH	K ₀	1.00 ± 0.05	0.039 ± 0.002
	PITCH	P	4.00 ± 0.10	0.157 ± 0.004
	BOTTOM HOLE DIAMETER	D ₁	1.00 ± 0.25	0.039 ± 0.002
PERFORATION	DIAMETER	D	1.50 ± 0.10	0.060 ± 0.004
	PITCH	P ₀	4.00 ± 0.10	0.157 ± 0.004
	POSITION	E	1.75 ± 0.10	0.069 ± 0.004
COVER TAPE	WIDTH	W	8.00 + 0.30 8.00 - 0.10	0.315 ± 0.012 0.315 ± 0.004
	THICKNESS	t ₁	0.254 ± 0.02	0.010 ± 0.0008
DISTANCE	CAVITY TO PERFORATION (WIDTH DIRECTION)	F	3.50 ± 0.05	0.138 ± 0.002
	CAVITY TO PERFORATION (LENGTH DIRECTION)	P ₂	2.00 ± 0.05	0.079 ± 0.002

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Obsoletes 5988-9368EN

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